

L660N-50M32L

High Power Red LED

L660N-50M32L is an AlGaInP LED mounted on TO-18 stem and hermetically sealed with glass ball lens can, is designed for high beam uses. On forward bias it emits a spectral band of radiation, which peaks at 660nm.

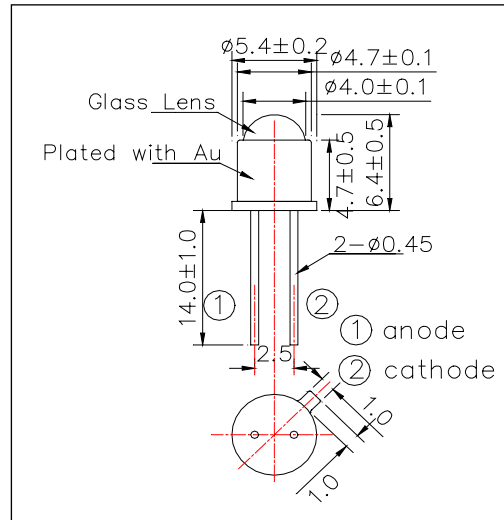
<Features>

- High Reliability
- High Power

<Specifications>

1. Product Name: LED Lamp
2. Type Number: L660N-50M32L
3. Chip:
 - Chip material: AlGaInP
 - Dimension: 500um x 500um
 - Peak Wavelength: 660nm
4. Package
 - Type: TO-18 Stem
 - Lens: Glass Ball Lens
 - Cap: Gold Plated

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Ta=25°C]			
Item	Symbol	Maximum Rated Value	Unit
Power Dissipation	PD	220	mW
Forward Current	IF	100	mA
Pulse Forward Current*	IFP	1000	mA
Reverse Voltage	VR	5	V
Thermal Resistance	Rthja	310	K/W
Operating Temperature	TOPR	-30 ~ +85	°C
Storage Temperature	TSTG	-40 ~ +100	°C
Soldering Temperature**	TSOL	265	°C

* Duty=1% and Pulse Width=10μs

* Soldering condition must be completed within 3 seconds at 265°C

Electro-Optical Characteristics						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=20mA		1.8	2.0	V
		IF=50mA		1.9	2.1	
Radiated Power*	PO	IF=20mA		7.6		mW
Radiant Intensity**	IE	IF=20mA		45		mW/sr
Brightness	IV	IF=20mA		3500		mcd
Peak Wavelength	λP	IF=20mA	650	660	670	nm
Half Width	Δλ	IF=20mA		15		nm
Viewing Half Angle	θ1/2	IF=20mA		±8		deg

* Measured by S3584-08

** Measured by Tektronix J-6512

